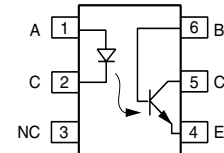
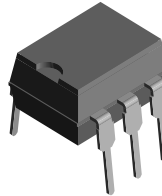


## Optocoupler, Phototransistor Output, With Base Connection

### Features

- Isolation Test Voltage 5300 V<sub>RMS</sub>
- Long Term Stability
- Industry Standard Dual-in-Line Package
- Lead-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### Agency Approvals

- Underwriters Lab File #E52744 System Code H or J
- DIN EN 60747-5-2 (VDE0884)  
DIN EN 60747-5-5 pending
- BSI IEC60950 IEC60065
- FIMKO

i179004



### Order Information

Part	Remarks
CNY17-1	CTR 40 - 80 %, DIP-6
CNY17-2	CTR 63 - 125 %, DIP-6
CNY17-3	CTR 100 - 200 %, DIP-6
CNY17-4	CTR 160 - 320 %, DIP-6
CNY17-1X006	CTR 40 - 80 %, DIP-6 400 mil (option 6)
CNY17-1X007	CTR 40 - 80 %, SMD-6 (option 7)
CNY17-1X009	CTR 40 - 80 %, SMD-6 (option 9)
CNY17-2X006	CTR 63 - 125 %, DIP-6 400 mil (option 6)
CNY17-2X007	CTR 63 - 125 %, SMD-6 (option 7)
CNY17-2X009	CTR 63 - 125 %, SMD-6 (option 9)
CNY17-3X006	CTR 100 - 200 %, DIP-6 400 mil (option 6)
CNY17-3X007	CTR 100 - 200 %, SMD-6 (option 7)
CNY17-3X009	CTR 100 - 200 %, SMD-6 (option 9)
CNY17-4X006	CTR 160 - 320 %, DIP-6 400 mil (option 6)
CNY17-4X007	CTR 160 - 320 %, SMD-6 (option 7)
CNY17-4X009	CTR 160 - 320 %, SMD-6 (option 9)

For additional information on the available options refer to Option Information.

### Description

The CNY17 is an optically coupled pair consisting of a Gallium Arsenide infrared emitting diode optically coupled to a silicon NPN phototransistor.

Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output.

The CNY17 can be used to replace relays and transformers in many digital interface applications, as well as analog applications such as CRT modulation.

### Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

### Input

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		$V_R$	6.0	A
Forward current		$I_F$	60	mA
Surge current	$t \leq 10\text{ }\mu\text{s}$	$I_{FSM}$	2.5	A
Power dissipation		$P_{diss}$	100	mW

### Output

Parameter	Test condition	Symbol	Value	Unit
Collector-emitter breakdown voltage		$BV_{CEO}$	70	V
Emitter-base breakdown voltage		$BV_{EBO}$	7.0	V
Collector current		$I_C$	50	mA
	$t < 1.0\text{ ms}$	$I_C$	100	mA
Power dissipation		$P_{diss}$	150	mW

### Coupler

Parameter	Test condition	Symbol	Value	Unit
Isolation test voltage (between emitter & detector referred to climate DIN 50014, part 2, Nov. 74)	$t = 1\text{ sec}$	$V_{ISO}$	5300	$V_{RMS}$
Creepage distance			$\geq 7.0$	mm
Clearance distance			$\geq 7.0$	mm
Isolation thickness between emitter and detector			$\geq 0.4$	mm
Comparative tracking index per DIN IEC 112/VDE0303, part 1			175	
Isolation resistance	$V_{IO} = 500\text{ V}, T_{amb} = 25\text{ }^{\circ}\text{C}$	$R_{IO}$	$\geq 10^{12}$	$\Omega$
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ }^{\circ}\text{C}$	$R_{IO}$	$\geq 10^{11}$	$\Omega$
Storage temperature		$T_{stg}$	- 55 to + 150	$^{\circ}\text{C}$
Operating temperature		$T_{amb}$	- 55 to + 100	$^{\circ}\text{C}$
Soldering temperature	max. 10 s, dip soldering: distance to seating plane $\geq 1.5\text{ mm}$	$T_{sld}$	260	$^{\circ}\text{C}$

### Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

### Input

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 60\text{ mA}$	$V_F$		1.25	1.65	V
Breakdown voltage	$I_R = 10\text{ mA}$	$V_{BR}$	6.0			V
Reserve current	$V_R = 6.0\text{ V}$	$I_R$		0.01	10	$\mu\text{A}$
Capacitance	$V_R = 0\text{ V}$ , $f = 1.0\text{ MHz}$	$C_O$		25		pF
Thermal resistance		$R_{th}$		750		K/W

### Output

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector-emitter capacitance	$V_{CE} = 5.0\text{ V}$ , $f = 1.0\text{ MHz}$	$C_{CE}$		5.2		pF
Collector - base capacitance	$V_{CB} = 5.0\text{ V}$ , $f = 1.0\text{ MHz}$	$C_{CB}$		6.5		pF
Emitter - base capacitance	$V_{EB} = 5.0\text{ V}$ , $f = 1.0\text{ MHz}$	$C_{EB}$		7.5		pF
Thermal resistance		$R_{th}$		500		K/W

### Coupler

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Collector-emitter saturation voltage	$V_F = 10\text{ mA}$ , $I_C = 2.5\text{ mA}$		$V_{CEsat}$		0.25	0.4	V
Coupling capacitance			$C_C$		0.6		pF
Collector-emitter leakage current	$V_{CE} = 10\text{ V}$ , $I_{CEO}$	CNY17-1	$I_{CEO}$		2.0	50	nA
		CNY17-2	$I_{CEO}$		2.0	50	nA
		CNY17-3	$I_{CEO}$		5.0	100	nA
		CNY17-4	$I_{CEO}$		5.0	100	nA

### Current Transfer Ratio

Current Transfer Ratio and collector-emitter leakage current by dash number ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ )

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
$I_C/I_F$	$I_F = 10\text{ mA}$ , $V_{CE} = 5.0\text{ V}$	CNY17-1	CTR	40		80	%
		CNY17-2	CTR	63		125	%
		CNY17-3	CTR	100		200	%
		CNY17-4	CTR	160		320	%
	$I_F = 1.0\text{ mA}$ , $V_{CE} = 5.0\text{ V}$	CNY17-1	CTR	13	30		%
		CNY17-2	CTR	22	45		%
		CNY17-3	CTR	34	70		%
		CNY17-4	CTR	56	90		%